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April 1st, 2010 Renesas Electronics Corporation

Issued by: Renesas Electronics Corporation (http://www.renesas.com)

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MOS FIELD EFFECT TRANSISTOR μ PA1970

N-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

DESCRIPTION

The $\mu\,\mathrm{PA1970}$ is a switching device which can be driven directly by a 2.5 V power source.

The device features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

FEATURES

- 2.5 V drive available
- Low on-state resistance

RDS(on)1 = 69 m Ω MAX. (VGS = 4.5 V, ID = 1.0 A)

 $R_{DS(on)2} = 72 \text{ m}\Omega \text{ MAX.} (V_{GS} = 4.0 \text{ V}, I_{D} = 1.0 \text{ A})$

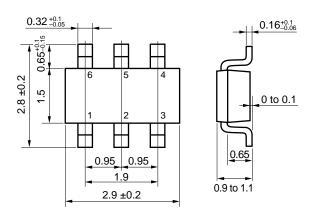
 $R_{DS(on)3} = 107 \text{ m}\Omega \text{ MAX}. \text{ (Vgs} = 2.5 \text{ V, ID} = 1.0 \text{ A)}$

ORDERING INFORMATION

PART NUMBER	PACKAGE
μPA1970TE Note	SC-95 (Mini Mold Thin Type)

Note Marking: TT

PACKAGE DRAWING (Unit: mm)



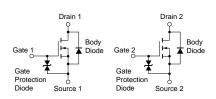
- 6: Drain 1 1: Gate 1
- 4: Drain 2 3: Gate 2
- Gate 1 Source 1

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (Vgs = 0 V)	V_{DSS}	20	V
Gate to Source Voltage (VDS = 0 V)	Vgss	±12	V
Drain Current (DC) (TA = 25°C)	$I_{D(DC)}$	±2.2	Α
Drain Current (pulse) Note1	I _{D(pulse)}	±8.8	Α
Total Power Dissipation (2 units) (T _A = 25°C) ^{Note2}	P _{T1}	1.15	W
Total Power Dissipation (1 unit) (T _A = 25°C) ^{Note2}	P _{T2}	0.57	W
Channel Temperature	Tch	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C

EQUIVALENT CIRCUITS

Source 2



- **Notes 1.** PW \leq 10 μ s, Duty Cycle \leq 1%
 - **2.** Mounted on FR-4 board of 5000 mm² x 1.1 mm, $t \le 5$ sec.

Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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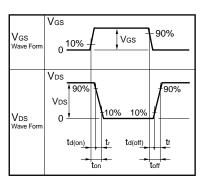


ELECTRICAL CHARACTERISTICS (TA = 25°C)

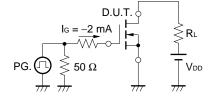
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 20 V, V _{GS} = 0 V			10	μΑ
Gate Leakage Current	Igss	$V_{GS} = \pm 12 \text{ V}, V_{DS} = 0 \text{ V}$			±10	μΑ
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1.0 mA	0.5	0.97	1.5	V
Forward Transfer Admittance	y fs	VDS = 10 V, ID = 1.0 A	1.0	3.3		S
Drain to Source On-state Resistance	RDS(on)1	Vgs = 4.5 V, ID = 1.0 A		55	69	mΩ
	RDS(on)2	Vgs = 4.0 V, ID = 1.0 A		57	72	mΩ
	RDS(on)3	Vgs = 2.5 V, ID = 1.0 A		80	107	mΩ
Input Capacitance	Ciss	V _{DS} = 10 V		160		pF
Output Capacitance	Coss	V _{GS} = 0 V		60		pF
Reverse Transfer Capacitance	Crss	f = 1.0 MHz		40		pF
Turn-on Delay Time	td(on)	V _{DD} = 10 V, I _D = 1.0 A		17		ns
Rise Time	tr	V _{GS} = 4.0 V		90		ns
Turn-off Delay Time	td(off)	R _G = 10 Ω		100		ns
Fall Time	tf			120		ns
Total Gate Charge	Qg	V _{DD} = 16 V		2.3		nC
Gate to Source Charge	Qgs	V _{GS} = 4.0 V		0.5		nC
Gate to Drain Charge	QgD	I _D = 2.2 A		1.1		nC
Body Diode Forward Voltage	V _{F(S-D)}	IF = 2.2 A, VGS = 0 V		0.85		V

TEST CIRCUIT 1 SWITCHING TIME

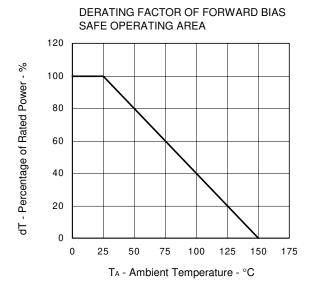
PG. R_{G} $V_{GS(-)}$ 0 $\tau = 1 \mu s$ Duty Cycle $\leq 1\%$

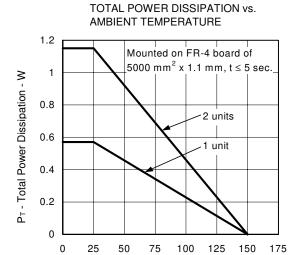


TEST CIRCUIT 2 GATE CHARGE



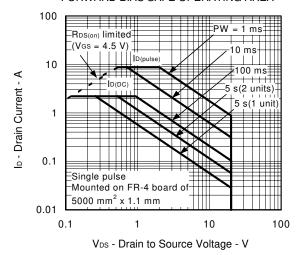
TYPICAL CHARACTERISTICS (TA = 25°C)



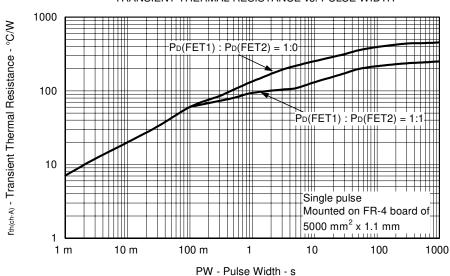


TA - Ambient Temperature - °C

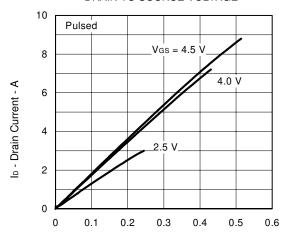
FORWARD BIAS SAFE OPERATING AREA



TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

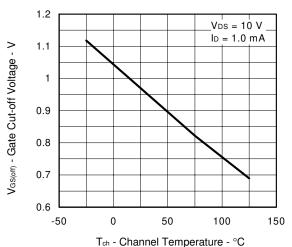


DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE

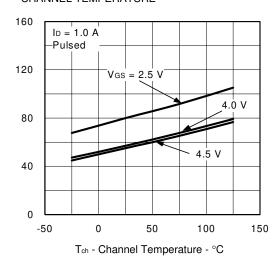


VDS - Drain to Source Voltage - V

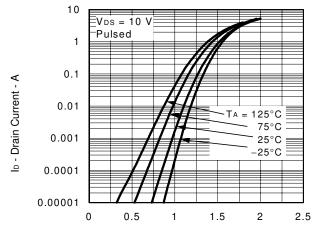
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE

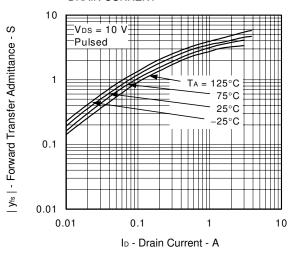


FORWARD TRANSFER CHARACTERISTICS

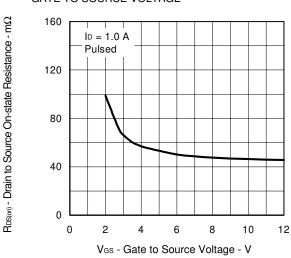


V_{GS} - Gate to Source Voltage - V

FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

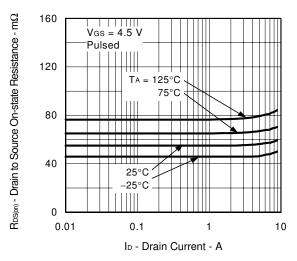


R_{DS(m)} - Drain to Source On-state Resistance - mΩ

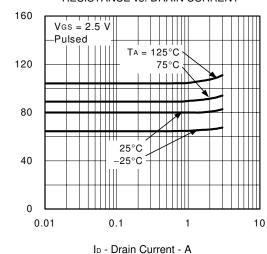
R_{DS(o1)} - Drain to Source On-state Resistance - mΩ

Cisc, Coss, Crss - Capacitance - pF

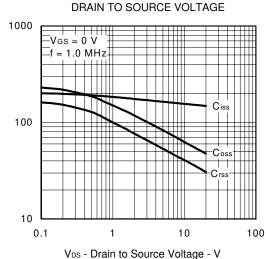
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



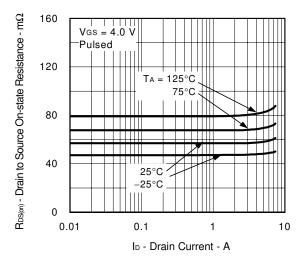
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



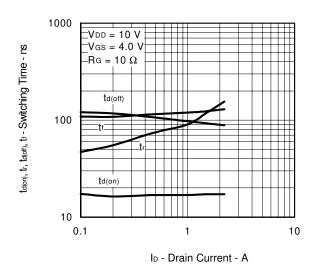
CAPACITANCE vs.



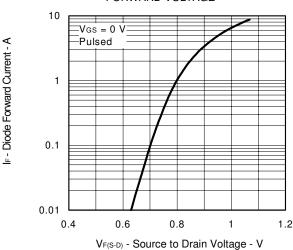
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



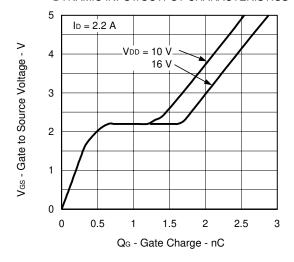
SWITCHING CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



DYNAMIC INPUT/OUTPUT CHARACTERISTICS



NEC μ PA1970

[MEMO]

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